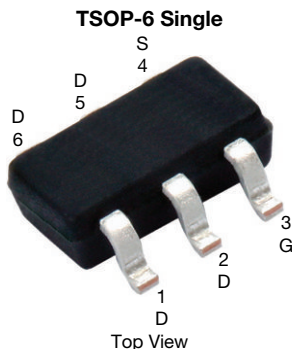


# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

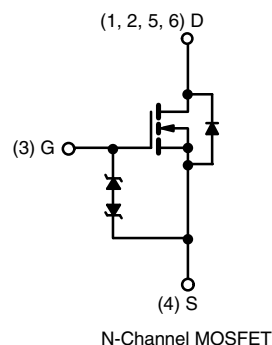


## FEATURES

- TrenchFET® power MOSFET
- Typical ESD protection 800 V HBM
- AEC-Q101 qualified
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**



## PRODUCT SUMMARY

$V_{DS}$ (V)	60
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10$ V	0.042
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.063
$I_D$ (A)	7
Configuration	Single

Marking Code: 91XXX

## ORDERING INFORMATION

Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3426CEEV (for detailed order number please see <a href="http://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	60	V
Gate-source voltage	$V_{GS}$	$\pm 20$	
Continuous drain current	$I_D$	$T_C = 25$ °C	7
		$T_C = 125$ °C	4
Continuous source current (diode conduction)	$I_S$	4.6	A
Pulsed drain current <sup>a</sup>	$I_{DM}$	29	
Single pulse avalanche current	$I_{AS}$	10	
Single pulse avalanche energy	$E_{AS}$	5	mJ
Maximum power dissipation	$P_D$	$T_C = 25$ °C	5
		$T_C = 125$ °C	1.6
Operating junction and storage temperature range	$T_J, T_{stg}$	- 55 to +175	°C

## THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	$R_{thJA}$	110	°C/W
Junction-to-foot (drain)	$R_{thJF}$	30	

### Notes

- a. Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %  
b. When mounted on 1" square PCB (FR4 material)

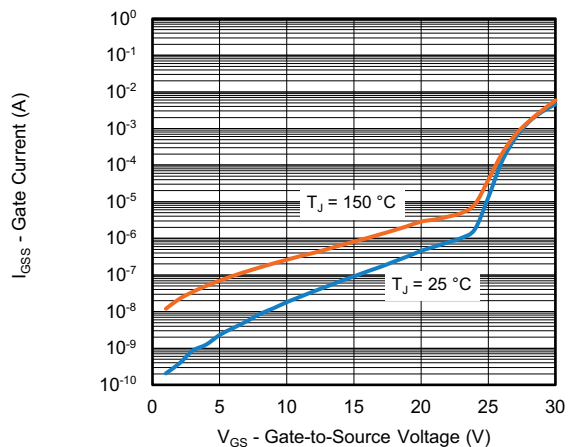
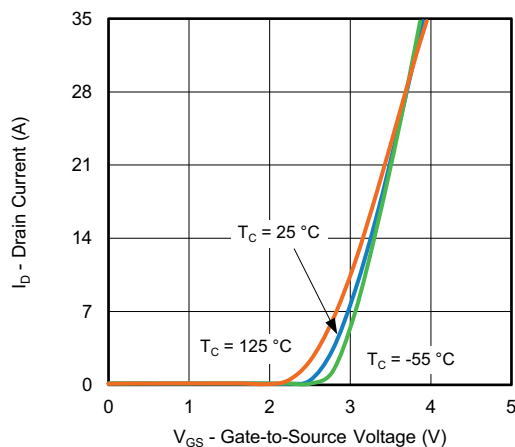
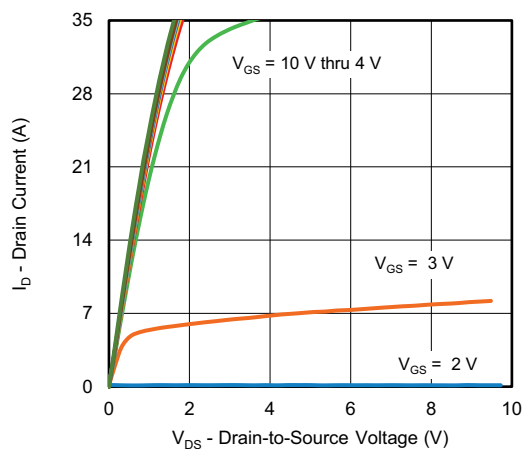
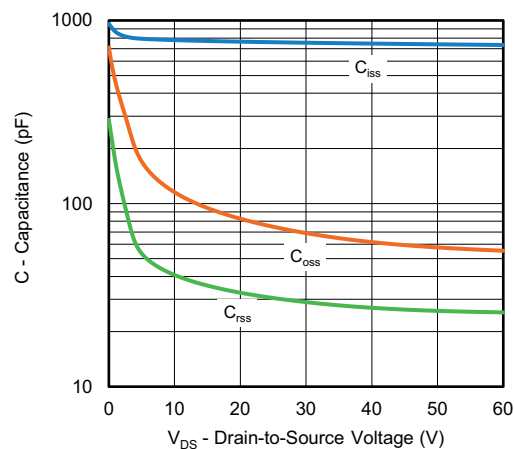
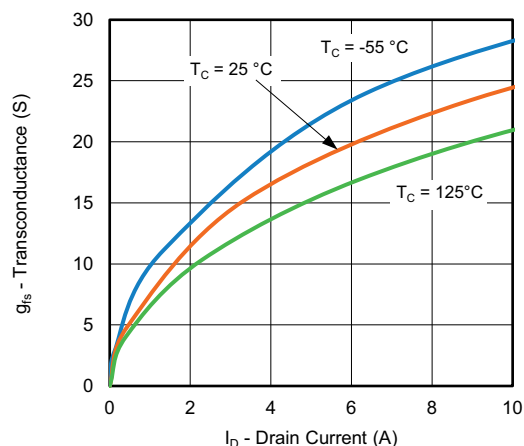
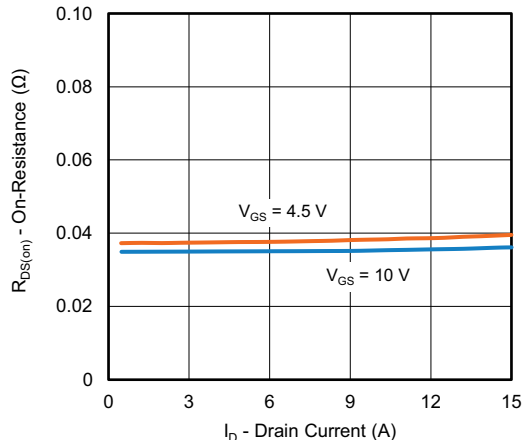


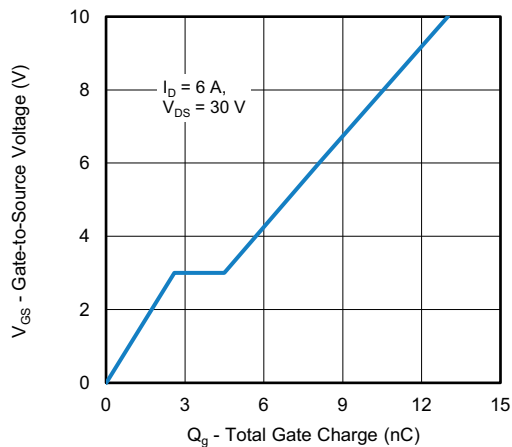
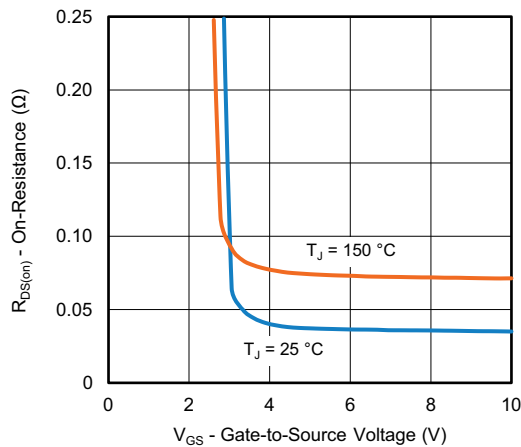
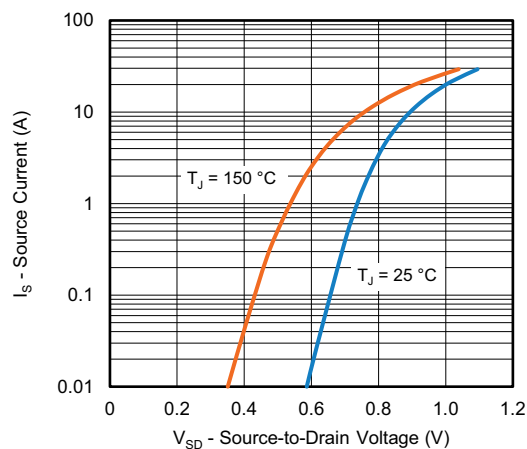
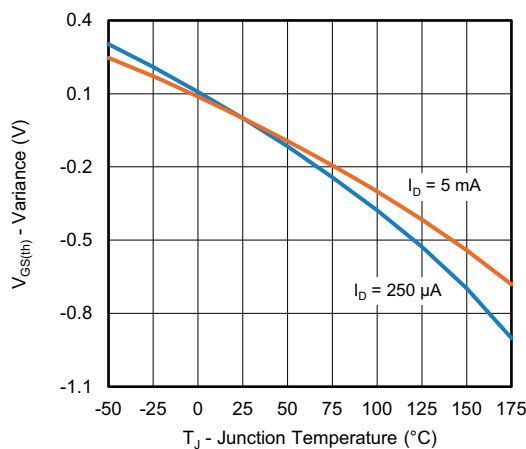
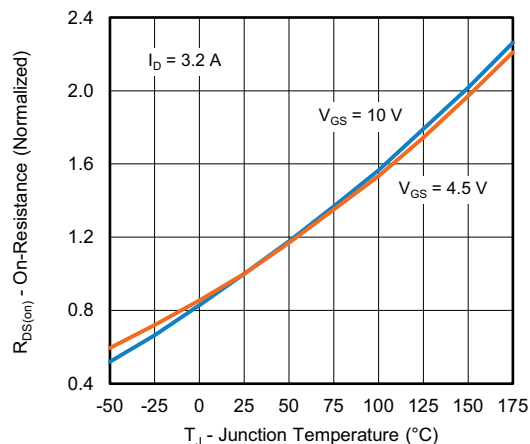
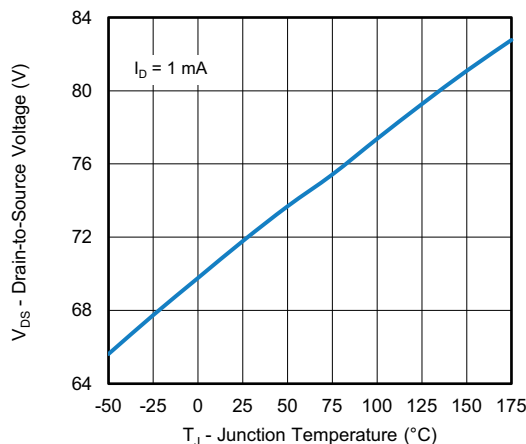
SPECIFICATIONS (T <sub>C</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA		60	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		1.5	2.0	2.5	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V		-	-	± 500	nA
		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V		-	-	± 1	mA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1	μA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> ≥ 5 V	10	-	-	A
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5 A	-	0.0351	0.042	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5 A, T <sub>J</sub> = 125 °C	-	0.0627	-	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5 A, T <sub>J</sub> = 175 °C	-	0.0793	-	
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 4 A	-	0.038	0.063	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 4 A		-	16	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 30 V, f = 1 MHz	-	756	1100	pF
Output capacitance	C <sub>oss</sub>			-	69	100	
Reverse transfer capacitance	C <sub>rss</sub>			-	29	55	
Total gate charge <sup>c</sup>	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 6 A	-	13	19.5	nC
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>			-	2.6	-	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	1.9	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz		1.9	3.83	5.7	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 30 V, R <sub>L</sub> = 7.5 Ω I <sub>D</sub> ≅ 4 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω		-	7	10	ns
Rise time <sup>c</sup>	t <sub>r</sub>			-	4	14	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	18	25	
Fall time <sup>c</sup>	t <sub>f</sub>			-	4	6	
Source-Drain Diode Ratings and Characteristics <sup>b</sup>							
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	29	A
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = 1.6 A, V <sub>GS</sub> = 0		-	0.76	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 1.7 A, di/dt = 100 A/μs		-	18	36	ns
Body diode reverse recovery charge	Q <sub>rr</sub>			-	14	28	nC
Reverse recovery fall time	t <sub>a</sub>			-	14	-	ns
Reverse recovery rise time	t <sub>b</sub>			-	4	-	
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-1.76	-	A

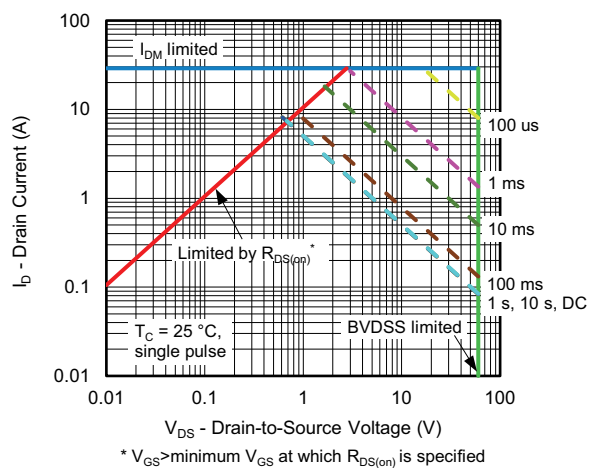
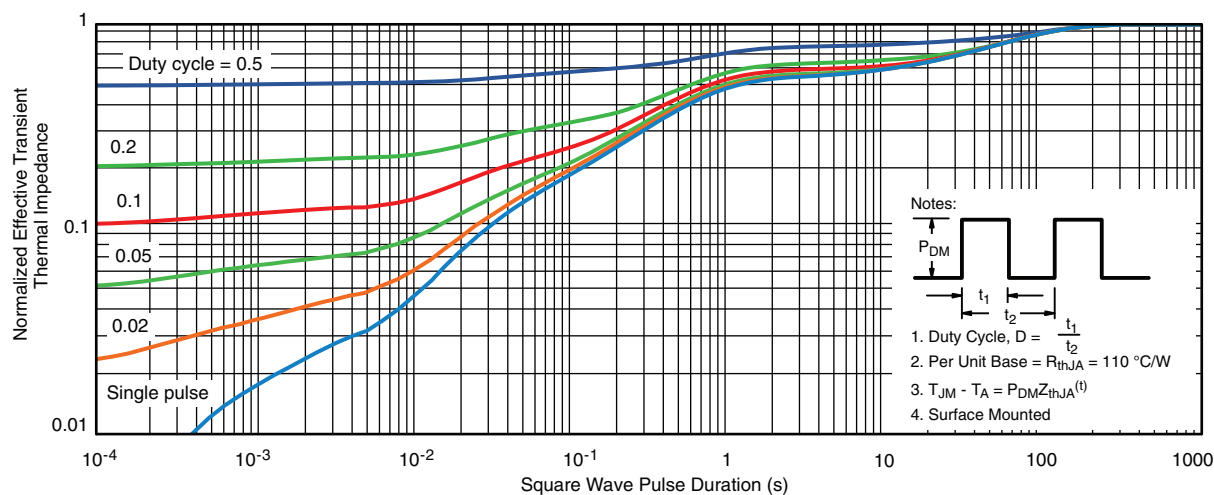
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing  
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

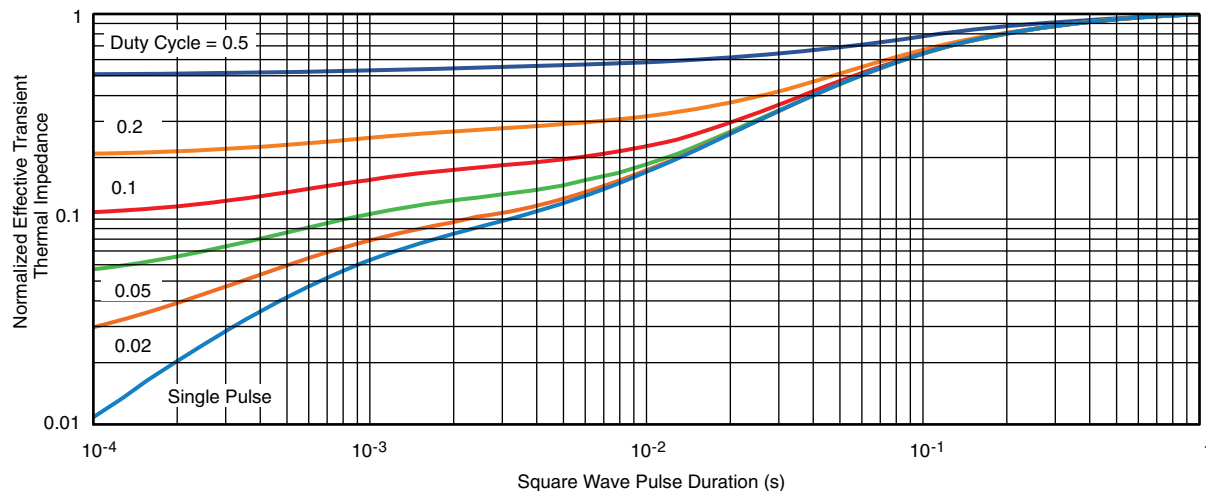
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

**Gate Current vs. Gate-Source Voltage**

**Transfer Characteristics**

**Output Characteristics**

**Capacitance**

**Transconductance**

**On-Resistance vs. Drain Current**

**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

**Gate Charge**

**On-Resistance vs. Gate-Source Voltage**

**Source-Drain Diode Forward Voltage**

**Threshold Voltage**

**On-Resistance vs. Junction Temperature**

**Drain-Source Breakdown vs. Junction Temperature**

**THERMAL RATINGS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

**Safe Operating Area**

**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**THERMAL RATINGS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)



**Normalized thermal Transient Impedance, Junction-to-Foot**

**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient ( $25\text{ }^{\circ}\text{C}$ )
  - Normalized Transient Thermal Impedance Junction-to-Foot ( $25\text{ }^{\circ}\text{C}$ )are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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## TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C



5-LEAD TSOP



6-LEAD TSOP



	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ <sub>1</sub>	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						

## Recommended Land Pattern For TSOP-5L / TSOP-6L



TSOP 5L



TSOP 6L


**Note**

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022  
DWG: 3010





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